











CDCE62002

SCAS882E - JUNE 2009-REVISED OCTOBER 2016

# CDCE62002 Four Output Clock Generator/Jitter Cleaner With Integrated Dual VCOs

### Features

- Frequency Synthesizer With PLL/VCO and Partially Integrated Loop Filter
- Fully Configurable Outputs Including Frequency and Output Format
- Smart Input Multiplexer Automatically Switches Between One of Two Reference Inputs
- Multiple Operational Modes Include Clock Generation Through Crystal, SERDES Start-Up Mode, Jitter Cleaning, and Oscillator Based Holdover Mode
- Integrated EEPROM Determines Device Configuration at Power Up
- **Excellent Jitter Performance**
- Integrated Frequency Synthesizer Including PLL, Multiple VCOs, and Loop Filter:
  - Full Programmability Facilitates Phase Noise Performance Optimization Enabling Jitter Cleaner Mode
  - Programmable Charge Pump Gain and Loop Filter Settings
  - Unique Dual-VCO Architecture Supports a Wide Tuning Range 1.750 GHz to 2.356 GHz.
- Universal Output Blocks Support Up to 2 Differential, 4 Single-Ended, or Combinations of Differential or Single-Ended:
  - 0.5 ps RMS (10 kHz to 20 MHz) Output Jitter Performance
  - Low Output Phase Noise: –130 dBc/Hz at 1 MHz Offset, Fc = 491.52 MHz
  - Output Frequency Ranges From 10.94 MHz to 1.175 GHz in Synthesizer Mode
  - LVPECL, LVDS, and LVCMOS
  - Independent Output Dividers Support Divide Ratios for 1, 2, 3, 4, 5, 8, 10, 12, 16, 20, 24, and 32
- Flexible Inputs With Innovative Smart Multiplexer:
  - Two Universal Differential Inputs Accept Frequencies from 1 MHz up to 500 MHz (LVPECL), 500 MHz (LVDS), or 250 MHz (LVCMOS)
  - One Auxiliary Input Accepts Crystals in the Range of 2 MHz to 42 MHz
  - Clock Generator Mode Using Crystal Input
  - Smart Input Multiplexer Can be Configured to Automatically Switch Between Highest Priority Clock Source Available Allowing for Fail-Safe

#### Operation

- Typical Power Consumption 750 mW at 3.3 V
- Integrated EEPROM Stores Default Settings: Therefore, the Device Can Power Up in a Known, **Predefined State**
- Offered in QFN-32 Package
- ESD Protection Exceeds 2000 V HBM
- Industrial Temperature Range: -40°C to +85°C

# Applications

- Data Converter and Data Aggregation Clocking
- Wireless Infrastructure
- Switches and Routers
- **Medical Electronics**
- Military and Aerospace
- Industrial
- Clock Generation and Jitter Cleaning

# 3 Description

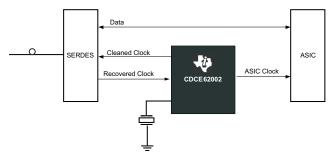
The CDCE62002 device is a high-performance clock generator featuring low output jitter, a high degree of through a SPI interface, configurability programmable start-up modes determined by on-chip EEPROM. Specifically tailored for clocking data converters and high-speed digital signals, the CDCE62002 achieves jitter performance under 0.5 ps RMS (1).

## Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE (NOM)	
CDCE62002	VQFN (32)	5.00 mm × 5.00 mm	

(1) For all available packages, see the orderable addendum at the end of the data sheet.

## CDCE62002 Application Example



(1) 10-kHz to 20-MHz integration bandwidth.



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# 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Ch	anges from Revision D (February 2012) to Revision E	Page
•	Added figure cross references to Electrical Tables	8
•	Added figure titles	12
•	Updated Figure 18	19
•	Updated Figure 20	20
•	Corrected description for bits 0 and 1 in CDCE62002 Register 0 Bit Definitions	36
•	Corrected the register bits for LVPECL-AC, LVPECL-DC, LVDS-AC, LVDS-DC reference inputs in <i>Reference Input AC/DC Input Termination Table</i>	

С	hanges from Revision C (March 2011) to Revision D	Page
•	Added 3 rows in TIMING REQUIREMENTS table, under Duty Cycle row	9
•	Added a sentence below Equation 3	16
•	Changed last row last column in Figure 23 truth table from Disabled to Input Buffer Termination Disabled	20
•	Changed in Table 13, second column, 5th and 6th row from 1 to 0	23
•	Added a reference to Table 11 and 2 references to Table 12 in Table 6	36
•	Added 6 crossreferences to Table 8	37
•	Changed changed last row in Table 8 Description column, from "always reads 1" to "May read back to 1 or 0"	37

C	hanges from Revision B (February 2010) to Revision C	Page
•	Changed the description of Pin 30, REF_IN	6
•	Changed Pin 7 to open drain in Pin Functions table	6
•	Changed the description of Pin 19, TESTSYNC To: Reserved Pinresistor	6
•	Changed pin 31 From: Power To: A. Power in <i>Pin Functions</i> table	6
•	Changed Pin Functions table, Pins 9, 12 to VCC_OUT0. Pins 13 and 16 to VCC_OUT1	6
•	Changed Note1 of the Pin Functions table	6

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•	Deleted Dividers and from ELEC CHARACTERISTICS table in row P <sub>OFF</sub>	7
•	Changed Crytal input section first row From: Crystal Load Capacitance To: On-chip Load Capacitance	<mark>7</mark>
•	Added SPI OUTPUT row From: PLL To: PLL_LOCK	8
•	Changed t <sub>r</sub> / t <sub>f</sub> Max value From: 735 To: 135	9
•	Deleted (Reg 0 RAM bit 9 = 1) and (Reg 0 RAM bit 9 = 0) from the TIMING REQUIREMENTS table	9
•	Added Driver Level and Max shunt capacitance to AUXILARY_IN REQUIREMENT in the TIMING REQUIREMENT table	
•	Deleted Columns from Table 1: LVDS-HP and LVCMOS-HP	17
•	Changed Table 2	17
•	Changed the OUTPUT TO OUTPUT ISOLATION section	17
•	Deleted the SPI CONTROL INTERFACE TIMING section	18
•	Updated Figure 18	19
•	Updated Reference Input Buffer	20
•	Updated Figure 20	20
•	Changed the Smart Multiplexer Dividers section	21
•	Changed Changed the text in the Smart Multiplexer Divider section	21
•	Changed Figure 24	23
•	Deleted column 3 db Corner C3R3 from Table 12	27
•	Added sections: VCO Calibration, Crystal Input Interface, and Startup Time	29
•	Changed Figure 29	31
•	Changed the INTERFACE AND CONTROL BLOCK section	33
•	Changed figure Figure 36	35
•	Changed Table 17, RAM BITS To REGISTER BITS	37
•	Deleted the First four rows in Table 18 and the first column	37
•	Deleted (6 settings+DisAble+Enable) in Register bit 19 of Table 18	37
•	Added; set '0' to TI use Only in bit 26 in Table 18	37
•	Changed the description of bit 27 in Table 18	37
•	Deleted the First four rows in Table 19 and the first column	38
•	Added Receiving Notification of Documentation Updates section	41
CI	nanges from Revision A (July, 2009) to Revision B	Page
_		
•	Deleted feature reference to Single Ended Clock Source or Crystal and LVCMOS Input of up to 75 MHz	
•	Deleted references to single ended inputs and CMOS clock from description.	
•	Changed the description of Pin 2, AUX_IN	
•	Deleted LVCMOS INPUT MODE (AUX_IN) section from Electrical Characteristics	
•	Changed Crystal Shunt Capacitance to Crystal Load Capacitance with a MIN value of 8	
•	Deleted LVCMOS INPUT MODE (AUX_IN) section from Electrical Characteristics	
•	Deleted LVCMOS INPUT MODE (AUX_IN) section from Electrical Characteristics	
•	Deleted f <sub>REF - Single</sub> paramter from AUXILARY_IN_REQUIRMENTS	
•	Deleted references to EEPROM Locking from "Interface and Control Block" section	
•	Changed Auxiliary Input Port section	
•	Deleted External Feed Back Mode section	
•	Deleted External Feedback Option section	
•	Changed EXTFEEDBACK to RESERVED for bit 10 in Table 16	
•	Changed EELOCK to RESERVED for bit 30 in Table 18	37



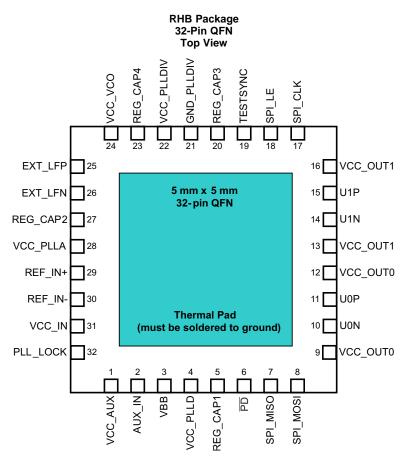
Changes from Original (June 2009) to Revision A		Page
Added information to Pin 18 description - The input has an intern	al 150-kΩ pull-up resist	6
Added NOTE: All VCC pins need to be connected for the device	to operate properly	6
<ul> <li>Changed P<sub>LVPECL</sub>, P<sub>LVDS</sub>, P<sub>LVCMOS</sub> and P<sub>OFF</sub> Unit values From: W</li> </ul>	To: mW	7
Deleted underscore before IN+		
Deleted 6 from 8006		
Changed Y4 to Y1		
Added t <sub>r</sub> / t <sub>f</sub> MIN, TYP, and MAX values		9
<ul> <li>Added (Reg 0 RAM bit 9 = 0) to f<sub>REF - Diff REF DIV</sub></li> </ul>		9
Changed graphic input naming		13
Changed graphic input naming		14
Changed REF into REF_IN		17
Changed graphic		18
Changed Table 4		18
Changed PDDRESET to PLLRESET, in Table 4		18
Changed Power_Down to PD, in Table 4		
Changed PRI_IN to REF_IN in Figure 19		
Changed PRI_IN to REF_IN		
Changed PRI_IN to REF_IN		31
Changed part number error		33
<ul> <li>Changed REFERENCE to REF_IN and AUXILARY to AUX_IN, 1</li> </ul>	able 16	36
Changed power to current		
<ul> <li>Changed the description of bits 0 - 5 To: TI Test Registers. For T</li> </ul>		



# 5 Description (continued)

It incorporates a synthesizer block with partially integrated loop filter, a clock distribution block including programmable output formats, and an input block featuring an innovative smart multiplexer. The clock distribution block includes two individually programmable outputs that can be configured to provide different combinations of output formats (LVPECL, LVDS, LVCMOS). Each output can also be programmed to a unique output frequency (ranging from 10.94 MHz to 1.175 GHz <sup>(1)</sup>). If Both outputs are configured in single-ended mode (such as LVCMOS), the CDCE62002 supports up to four outputs. The input block includes one universal differential inputs which support frequencies up to 500 MHz and an auxiliary input that can be configured to connect to an external AT-Cut crystal through an onboard oscillator block. The smart input multiplexer has two modes of operation, manual and automatic. In manual mode, the user selects the synthesizer reference through the SPI interface. In automatic mode, the input multiplexer will automatically select between the highest priority input clock available.

# 6 Pin Configuration and Functions



(1) Frequency range depends on operational mode and output format selected.



### **Pin Functions**

PIN			(1)		
NAME	NO.	TYPE	DESCRIPTION <sup>(1)</sup>		
AUX_IN	2	I	Auxiliary Input is a Crystal input pin that connect to an internal oscillator circuitry.		
EXT_LFN	26	Analog	External Loop Filter Input Negative.		
EXT_LFP	25	Analog	External Loop Filter Input Positive		
GND	PAD	Ground	Ground is on Thermal PAD. See Layout Guidelines		
GND_PLLDIV	21	Ground	Ground for PLL Divider circuitry. (short to GND)		
PD	6	ı	PD or Power-Down Pin is an active low pin and can be activated externally or through the corresponding Bit in SPI Register 2 While PD is asserted (low), the device is shut down. When PD switches high the EEPROM becomes loaded into the RAM. After the selected input clock signal becomes available, the VCO starts calibration and the PLL aims to achieve lock. All Output dividers become initiated. During self-calibration, the outputs are held static (for example, logical zero). PD pin has an internal 150-kΩ pullup resistor. Note: The SPI_LE signal has to be high in order for the EEPROM to load correctly into RAM on the Rising edge of PD.		
PLL_LOCK	32	0	PLL Lock indicator		
REF_IN+	29	1	Universal Input Buffer (LVPECL, LVDS, LVCMOS) positive input for the Reference Clock.		
REF_IN-	30	I	Universal Input Buffer (LVPECL, LVDS,) negative input for the Reference Clock. This pin must be pulled to ground through 1-k $\Omega$ resistor when input is selected LVCMOS.		
REG_CAP1	5	Analog	Capacitor for the internal Regulator. Connect to a 10-μF Capacitor (Y5V)		
REG_CAP2	27	Analog	Capacitor for the internal Regulator. Connect to a 10-μF Capacitor (Y5V)		
REG_CAP3	20	Analog	Capacitor for the internal Regulator. Connect to a 10-μF Capacitor (Y5V)		
REG_CAP4	23	Analog	Capacitor for the internal Regulator. Connect to a 10-μF Capacitor (Y5V)		
SPI_CLK	17	I	LVCMOS input, serial Control Clock Input for the SPI bus interface, with Hysteresis.		
SPI_LE	18	1	LVCMOS input, control Latch Enable for Serial Programmable Interface. Note: The SPI_LE signal has to be high in order for the EEPROM to load correctly on the Rising edge of $\overline{PD}$ . The input has an internal 150-k $\Omega$ pull-up resistor		
SPI_MISO	7	0	3-state LVCMOS Output that is enabled when SPI_LE is asserted low. It is the serial Data Output to the SPI bus interface.		
SPI_MOSI	8	I	LVCMOS input, Master Out Slave In as a serial Control Data Input to CDCE62002 for the SPI bus interface.		
TESTSYNC	19	I	Reserved Pin. Pull this pin down to ground using 1-k $\Omega$ resistor.		
U0P:U0N U1P:U1N	11,10 15,14	0	The outputs of <b>CDCE62002</b> are user definable and can be any combination of up to 2 LVPECL outputs, 2 LVDS outputs or up to 4 LVCMOS outputs. The outputs are selectable through SPI interface. The power-up setting is EEPROM configurable.		
VBB	3	Analog	Capacitor for the internal termination Voltage. Connect to a 1-μF Capacitor (Y5V)		
VCC_AUX	1	A. Power	3.3-V Supply Power for Crystal/Auxiliary Input Buffer Circuitry		
VCC_IN	31	A. Power	3.3-V Supply Power for Input Buffer Circuitry		
VCC_OUT0	9, 12	Dower	2.2 V. Cunnly for the Output Briffers		
VCC_OUT1	13, 16	Power	3.3-V Supply for the Output Buffers.		
VCC_PLLA	28	A. Power	3.3-V Supply Power for the PLL circuitry.		
VCC_PLLD	4	Power	3.3-V Supply Power for the PLL circuitry.		
VCC_PLLDIV	22	Power	3.3-V Supply Power for the PLL circuitry.		
VCC_VCO	24	A. Power	3.3-V Supply Power for the VCO circuitry.		

(1) It is furthermore recommended to use a supply filter for each VCC supply domain independently. A minimum requirement is to group the supplies into four independent groups:

VCC\_PLLA + VCC\_VCO

VCC\_PLLD + VCC\_PLLDIV

VCC\_IN + VCC\_AUXIN

VCC\_OUT0 + VCC\_OUT1

All VCC pins need to be connected for the device to operate properly.



# 7 Specifications

## 7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

		MIN	MAX	UNIT
	Supply voltage VCC <sup>(2)</sup>	-0.5		V
	Input voltage, V <sub>I</sub> <sup>(3)</sup>	-0.5		V
	Output voltage, V <sub>O</sub> <sup>(3)</sup>	-0.5		V
	Input current (V <sub>I</sub> < 0, V <sub>I</sub> > VCC)		±20	mA
	Output current for LVPECL/LVCMOS Outputs (0 < V <sub>O</sub> < V <sub>CC</sub> )		±50	mA
TJ	Junction temperature		125	°C
T <sub>stg</sub>	Storage temperature	-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute—maximum—rated conditions for extended periods may affect device reliability.

#### 7.2 Thermal Information

			CDCE62002	
	THERMAL METRIC <sup>(1)</sup>	QFN (RGZ)	UNIT	
		32 PINS		
		0-lfm Airflow	35	°C/W
	Junction-to-ambient thermal resistance (JEDEC Compliant Board - 3x3 vias on pad)	200-lfm Airflow	28.3	
	Board 5000 vias on pady	400-lfm Airflow	27.2	
$R_{\theta JP}$	Junction-to-pad		1.13	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

### 7.3 Electrical Characteristics

recommended operating conditions for the CDCE62002 Device for under the specified Industrial temperature range of -40°C to 85°C

	PARAMETER	TEST CONDITIONS	MIN	TYP <sup>(1)</sup>	MAX	UNIT
POWER SI	UPPLY					
	Supply voltage, $V_{CC\_OUT}$ , $V_{CC\_PLLDIV}$ , $V_{CC\_P}$	$_{ m LLD}$ , $ m V_{ m CC\_IN}$ , and $ m V_{ m CC\_AUX}$	3	3.3	3.6	V
	Analog supply voltage, VCC_PLLA, & VCC	3	3.3	3.6	V	
P <sub>LVPECL</sub>	REF at 30.72 MHz, outputs are LVPECL	Output 1 = 491.52 MHz		850		mW
P <sub>LVDS</sub>	REF at 30.72 MHz, outputs are LVDS	Output 2 = 245.76 MHz In case of LVCMOS Outputs (1) =		750		mW
P <sub>LVCMOS</sub>	REF at 30.72 MHz, outputs are LVCMOS	245.76MHz		800		mW
P <sub>OFF</sub>	REF at 30.72 MHz	Outputs are disabled		450		mW
P <sub>PD</sub>		Device is powered down		40		mW
DIFFEREN	ITIAL INPUT MODE (REF_IN)					
	Differental Input amplitude, (VIN+ - VIN-)		0.1		1.3	V
	Common-mode input voltage, VIC		1.0		V <sub>CC</sub> -03	V
I <sub>IH</sub>	Differential input current high (no internal termination)	V <sub>I</sub> = V <sub>CC</sub> , V <sub>CC</sub> = 3.6 V			20	μА
I <sub>IL</sub>	Differential input current low (no internal termination)	V <sub>I</sub> = 0 V, V <sub>CC</sub> = 3.6 V	-20			μА
Input Capa	citance on REF_IN			3		pF
CRYSTAL	INPUT SPECIFICATIONS					
	On-chip load capacitance		8		10	pF
	Equivalent Series Resistance (ESR)				50	Ω

(1) All typical values are at VCC = 3.3 V, temperature = 25°C.

<sup>2)</sup> All supply voltages have to be supplied simultaneously.

<sup>(3)</sup> The input and output negative voltage ratings may be exceeded if the input and output clamp-current ratings are observed.



# **Electrical Characteristics (continued)**

recommended operating conditions for the CDCE62002 Device for under the specified Industrial temperature range of  $-40^{\circ}$ C to  $85^{\circ}$ C

	PARAMETER	TEST	CONDITIONS	MIN	TYP <sup>(1)</sup>	MAX	UNIT
LVCMOS IN	PUT MODE (SPI_CLK,SPI_MOSI,SPI_LE,	PD, REF_IN)					
V <sub>IL</sub>	Low-level input voltage LVCMOS			0		0.3 V <sub>CC</sub>	V
V <sub>IH</sub>	High-level input voltage LVCMOS			0.7 V <sub>CC</sub>		V <sub>cc</sub>	V
V <sub>IK</sub>	LVCMOS input clamp voltage	$V_{CC} = 3 \text{ V}, I_{I} = -18$			-1.2	V	
I <sub>IH</sub>	LVCMOS input current VI =	V <sub>CC</sub> , V <sub>CC</sub> = 3.6 V				20	μΑ
I <sub>IL</sub>	LVCMOS input (Except REF_IN)	$V_{I} = 0 V, V_{CC} = 3.6$	V	-10		-40	μΑ
I <sub>IL</sub>	LVCMOS input (REF_IN)	V <sub>I</sub> = 0 V, V <sub>CC</sub> = 3.6	V	-10		10	μΑ
Cı	Input capacitance (LVCMOS signals)	$V_I = 0 \text{ V or } V_{CC} = 3$			3		pF
SPI OUTPU	「(MISO) / PLL_LOCK						
I <sub>OH</sub>	High-level output current	$V_{CC} = 3.3 V,$	V <sub>O</sub> = 1.65 V		-30		mA
I <sub>OL</sub>	Low-level output current	$V_{CC} = 3.3 \text{ V},$	V <sub>O</sub> = 1.65 V		33		mA
$V_{OH}$	High-level output voltage for LVCMOS outputs	V <sub>CC</sub> = 3 V,	I <sub>OH</sub> = -100 μA	V <sub>CC</sub> -0.5			V
V <sub>OL</sub>	Low-level output voltage for LVCMOS outputs	V <sub>CC</sub> = 3 V,	I <sub>OH</sub> = 100 μA			0.3	V
Co	Output capacitance o MISO	$V_{CC} = 3.3 \text{ V}; V_{O} = 0$	V or V <sub>CC</sub>		3		pF
I <sub>OZH</sub>	3-state output current	$V_{O} = V_{CC}, V_{O} = 0 \text{ V}$			5		μА
I <sub>OZL</sub>	o state output current	$v_O - v_{CC}, v_O = 0 V$			<b>-</b> 5		μΑ
EEPROM							
EEcyc	Programming cycle of EEPROM			100	1000		Cycles
EEret	Data retention			10			Years
VBB ( INPU	T BUFFER INTERNAL TERMINATION VO	LTAGE REFERENCE	)				
$V_{BB}$	Input termination voltage	IBB = -0.2 mA, dep	pending on the setting	1.2		1.9	V
INPUT BUFI	FERS INTERNAL TERMINATION RESIST	ORS (REF_IN)					
	Termination resistance	Single-ended			5		kΩ
PHASE DET	ECTOR						
f <sub>CPmax</sub>	Charge pump frequency			0.04		40	MHz
LVCMOS							
f <sub>clk</sub>	Output frequency, see Figure 7	Load = 5 pF to GNI	D			250	MHz
V <sub>OH</sub>	High-level output voltage for LVCMOS outputs	V <sub>CC</sub> = min to max	I <sub>OH</sub> = -100 μA	V <sub>CC</sub> -0.5			V
V <sub>OL</sub>	Low-level output voltage for LVCMOS outputs	V <sub>CC</sub> = min to max	I <sub>OL</sub> = 100 μA			0.3	V
I <sub>OH</sub>	High-level output current	$V_{CC} = 3.3 \text{ V}$	V <sub>O</sub> = 1.65 V		-30		mA
I <sub>OL</sub>	Low-level output current	$V_{CC} = 3.3 \text{ V}$	V <sub>O</sub> = 1.65 V		33		mA
t <sub>sko</sub>	Skew, output to output For Y0 to Y1	Both outputs set at reference = 30.72 M			75		ps
Co	Output capacitance on Y0 to Y1	$V_{CC} = 3.3 \text{ V}; V_{O} = 0$	V or V <sub>CC</sub>		5		pF
l <sub>ozh</sub>	Tristate LVCMOS output current	$V_O = V_{CC}$			5		μΑ
l <sub>ozL</sub>	Tristate LVCMOS output current	$V_O = 0 V$			-5		μΑ
I <sub>OPDH</sub>	Power-down output current	$V_O = V_{CC}$				25	μΑ
I <sub>OPDL</sub>	Power-down output current	V <sub>O</sub> = 0 V				5	μΑ
Duty cycle	LVCMOS			45%		55%	
t <sub>slew-rate</sub>	Output rise/fall slew rate			3.6	5.2		V/ns
LVDS OUTP	UT	•					
f <sub>clk</sub>	Output frequency	Configuration load	(see Figure 8)	0		800	MHz
VOD	Differential output voltage	R <sub>L</sub> = 100 Ω		270		550	mV
$\Delta V_{\sf OD}$	LVDS VOD magnitude change					50	mV
V <sub>os</sub>	Offset voltage	-40°C to 85°C			1.24		V
	VOS magnitude change				40		mV
$\Delta V_{OS}$							

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# **Electrical Characteristics (continued)**

recommended operating conditions for the CDCE62002 Device for under the specified Industrial temperature range of  $-40^{\circ}$ C to  $85^{\circ}$ C

	PARAMETER	TEST CONDITIONS	MIN	TYP <sup>(1)</sup>	MAX	UNIT
	Short-cicuit Vout- to ground	VOUT = 0			27	mA
t <sub>sk(o)</sub>	Skew, output to output For Y0 to Y1	Both outputs set at 122.88 MHz reference = 30.72 MHz		10		ps
Co	Output capacitance on Y0 to Y1	V <sub>CC</sub> = 3.3 V; VO = 0 V or V <sub>CC</sub>		5		pF
I <sub>OPDH</sub>	Power-down output current	$V_O = V_{CC}$			25	μΑ
I <sub>OPDL</sub>	Power-down output current	$V_O = 0 V$			5	μΑ
	Duty cycle		45%		55%	
$t_r / t_f$	Rise and fall time	20% to 80% of V <sub>OPP</sub>	110	160	190	ps
LVCMOS-	TO-LVDS					
t <sub>skP_C</sub>	Output skew between LVCMOS and LVDS outputs	V <sub>CC</sub> /2 to crosspoint	1.4	1.7	2.0	ns
LVPECL C	OUTPUT					
f <sub>clk</sub>	Output frequency	Configuration load (see Figure 9 and Figure 10)	0		1175	MHz
V <sub>OH</sub>	LVPECL high-level output voltage	Load	V <sub>CC</sub> -1.1		V <sub>CC</sub> -0.88	V
V <sub>OL</sub>	LVPECL low-level output voltage	Load	V <sub>CC</sub> -2.02		V <sub>CC</sub> -1.48	V
VOD	Differential output voltage		510		870	mV
t <sub>sko</sub>	Skew, output to output For Y0 to Y1	Both outputs set at 122.88 MHz		15		ps
СО	Output capacitance on Y0 to Y1	$V_{CC} = 3.3 \text{ V}; \text{ VO} = 0 \text{ V or } V_{CC}$		5		pF
I <sub>OPDH</sub>	Power-down output current	$V_O = V_{CC}$			25	μΑ
I <sub>OPDL</sub>	Power-down output current	V <sub>O</sub> = 0 V			5	μΑ
	Duty cycle		45%		55%	
t <sub>r</sub> / t <sub>f</sub>	Rise and fall time	20% to 80% of V <sub>OPP</sub>	55	75	135	ps
LVDS-TO-	- LVPECL					
t <sub>skP_C</sub>	Output skew between LVDS and LVPECL outputs	Crosspoint to Crosspoint	130	200	280	ps
LVCMOS-	-TO- LVPECL					
t <sub>skP_C</sub>	Output skew between LVCMOS and LVPECL outputs	V <sub>CC</sub> /2 to Crosspoint	1.6	1.8	2.2	ns
LVPECL F	HI-PERFORMANCE OUTPUT					
$V_{OH}$	LVPECL high-level output voltage	Load	V <sub>CC</sub> -1.11		V <sub>CC</sub> -0.91	V
V <sub>OL</sub>	LVPECL low-level output voltage	Load	V <sub>CC</sub> -2.06		V <sub>CC</sub> -1.84	V
VOD	Differential output voltage		670		950	mV
t <sub>r</sub> / t <sub>f</sub>	Rise and fall time	20% to 80% of V <sub>OPP</sub>	55	75	135	ps

# 7.4 Timing Requirements

over recommended ranges of supply voltage, load and operating free-air temperature range (unless otherwise noted)

	PARAMETER	MIN	TYP	MAX	UNIT
REF_IN REQUIR	EMENTS			·	
f <sub>REF - Diff IN-DIV</sub>	Maximum clock frequency applied to reference divider when (Register 0 Bit 9 = 1)			500	MHz
f <sub>REF - Diff REF_DIV</sub>	Maximum clock frequency applied to reference divider when (Register 0 Bit 9 = 0)			250	MHz
f <sub>REF- Single</sub>	For single-ended Inputs ( LVCMOS) on REF_IN			250	MHz
Duty Cycle	Duty cycle of REF_IN	40%		60%	
INTERNAL TIMIN	IG REQUIREMENTS	•			
f <sub>SMUX</sub>	Maximum clock frequency applied to smart MUX input			250	MHz
f <sub>INDIV</sub>	Maximum clock frequency applied to input divider			200	MHz
AUXILARY_IN R	EQUIREMENTS				
f <sub>REF - Crystal</sub>	AT-Cut crystal input	2		42	MHz
	Drive level	0.1			mW



# **Timing Requirements (continued)**

over recommended ranges of supply voltage, load and operating free-air temperature range (unless otherwise noted)

PARAMETER	MIN	TYP	MAX	UNIT
Maximum shunt capacitance			7	pF
PD REQUIREMENTS				
$t_r/t_f$ Rise and fall time of the $\overline{PD}$ signal from 20% to 80% of $V_{CC}$			4	ns

# 7.5 SPI Bus Timing Characteristics

	PARAMETER	MIN	TYP	MAX	UNIT
f <sub>Clock</sub>	Clock frequency for the SPI_CLK			20	MHz
t <sub>1</sub>	SPI_LE to SPI_CLK setup time	10			ns
t <sub>2</sub>	SPI_MOSI to SPI_CLK setup time	10			ns
t <sub>3</sub>	SPI_MOSI to SPI_CLK hold time	10			ns
t <sub>4</sub>	SPI_CLK high duration	25			ns
t <sub>5</sub>	SPI_CLK low duration	25			ns
t <sub>6</sub>	SPI_CLK to SPI_LE hold time	10			ns
t <sub>7</sub>	SPI_LE pulse width	20			ns
t <sub>8</sub>	SPI_CLK to MISO data valid			10	ns
t <sub>9</sub>	SPI_LE to SPI_MISO data valid			10	ns

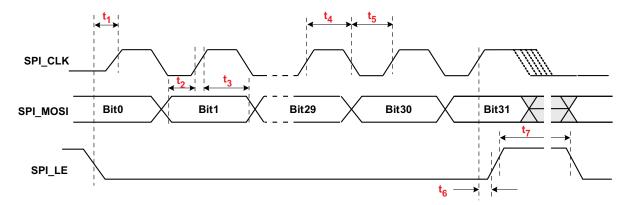


Figure 1. Timing Diagram for SPI Write Command

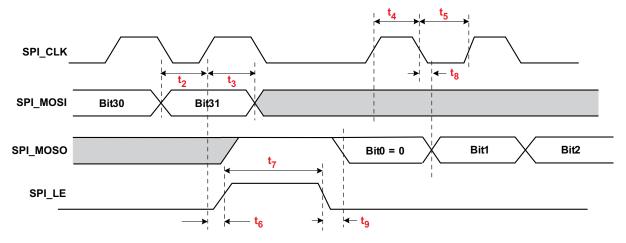
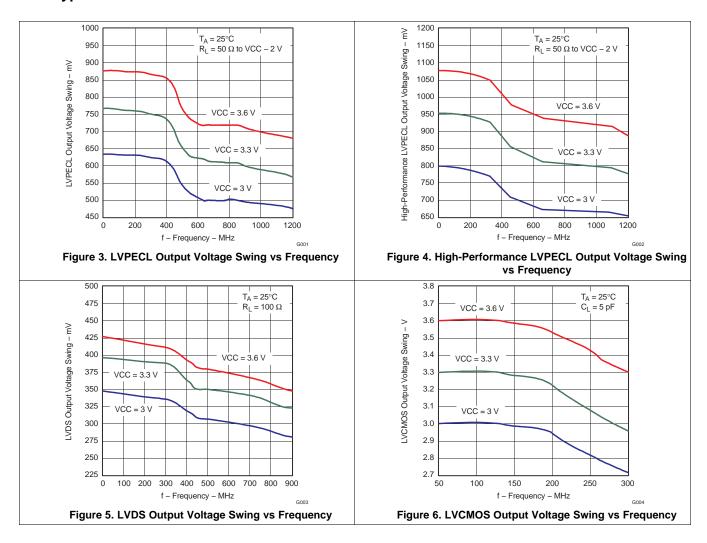


Figure 2. Timing Diagram for SPI Read Command



# 7.6 Typical Characteristics





# 8 Parameter Measurement Information

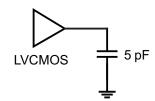


Figure 7. LVCMOS, 5 pF

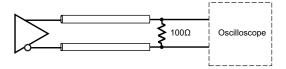


Figure 8. LVDS DC Termination Test

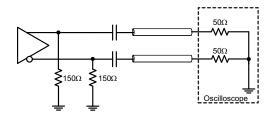


Figure 9. LVPECL AC Termination Test

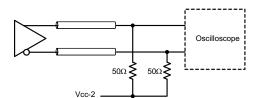


Figure 10. LVPECL DC Termination Test



# 9 Detailed Description

#### 9.1 Overview

The CDCE62002 comprises of four primary blocks: the interface and control block, the input block, the output block, and the synthesizer block. To determine which settings are appropriate for any specific combination of input and output frequencies, a basic understanding of these blocks is required. The interface and control block determines the state of the CDCE62002 at power up based on the contents of the onboard EEPROM. In addition to the EEPROM, the SPI port is available to configure the CDCE62002 by writing directly to the device registers after power up. The input block selects which of the two input ports is available for use by the synthesizer block. The output block provides two separate clock channels that are fully programmable. The synthesizer block multiplies and filters the input clock selected by the input block.

#### NOTE

This section of the data sheet provides a high-level description of the features of the CDCE62002 for purpose of understanding its capabilities. For a complete description of device registers and I/O, refer to the *Device Configuration* section.

# 9.2 Functional Block Diagrams

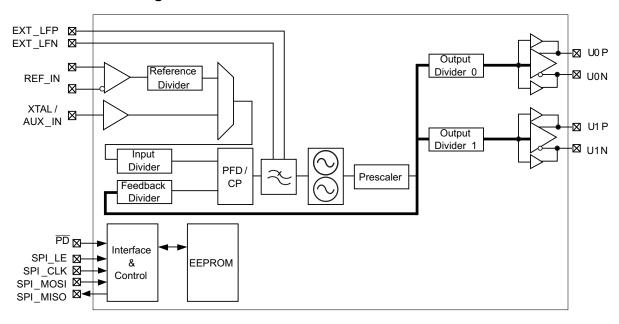


Figure 11. CDCE62002 Block Diagram



## **Functional Block Diagrams (continued)**

#### 9.2.1 Interface and Control Block

The CDCE62002 is a highly flexible and configurable architecture and as such contains a number of registers so that the user may specify device operation. The contents of three 28-bit wide registers implemented in static RAM determine device configuration at all times. On power up, the CDCE62002 copies the contents of the EEPROM into the RAM and the device begins operation based on the default configuration stored in the EEPROM. Systems that do not have a host system to communicate with the CDCE62002 use this method for device configuration. After power up, the host system may overwrite the contents of the RAM through the SPI (Serial Peripheral Interface) port. This enables the configuration and reconfiguration of the CDCE62002 during system operation. Finally, the device offers the ability to copy the contents of the RAM into EEPROM

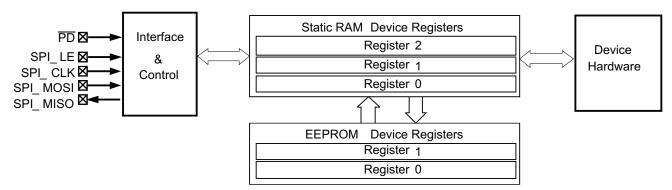


Figure 12. CDCE62002 Interface and Control Block

### 9.2.2 Input Block

The input block includes one universal input buffer and an auxiliary input. The input block buffers the incoming signals and facilitates signal routing to the Internal synthesizer block through the smart multiplexer (called the smart MUX). The CDCE62002 can divide the REF\_IN signal through the dividers present on the inputs of the first stage of the smart MUX.

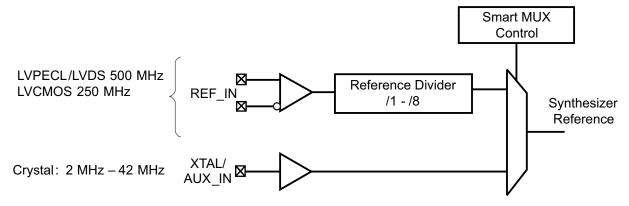


Figure 13. CDCE62002 Input Block



# **Functional Block Diagrams (continued)**

#### 9.2.3 Output Block

Both identical output blocks incorporate a clock divider module (CDM), and a universal output buffer. If an individual clock output channel is not used, then the user should disable the output buffer for the unused channel to save device power. Each channel includes 4-bit in register 0 to control the divide ratio. The output divider supports divide ratios from divide of 1 (bypass the divider) 2, 3, 4, 5, 8, 10, 12, 16, 20, 24, and 32.

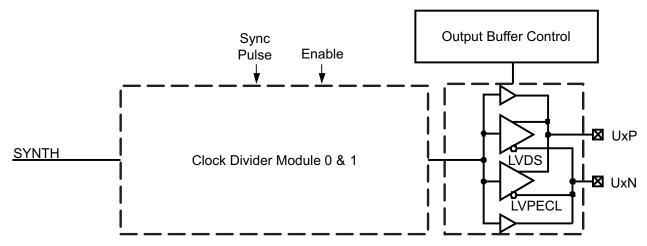


Figure 14. CDCE62002 Output Block

### 9.2.4 Synthesizer Block

Figure 15 presents a high-level overview of the synthesizer block on the CDCE62002. This block contains the phase-locked loop, internal loop filter, and dual voltage-controlled oscillators. Only one VCO is selected at a time. The loop is closed after a prescaler divider that feeds the output stage the feedback divider.

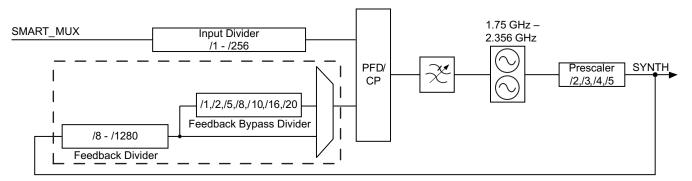


Figure 15. CDCE62002 Synthesizer Block

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# **Functional Block Diagrams (continued)**

# 9.2.5 Computing the Output Frequency

Figure 16 presents the block diagram of the CDCE62002 synthesizer highlighting the clock path for a single output. It also identifies the following regions containing dividers comprising the complete clock path:

- R: Is the Reference divider values.
- O: The output divider value (see Output Block for more details)
- I: The input divider value (see Synthesizer Block for more details)
- P: The Prescaler divider value (see Synthesizer Block of more details)
- F: The cumulative divider value of all dividers falling within the feedback divider (see *Synthesizer Block* for more details)

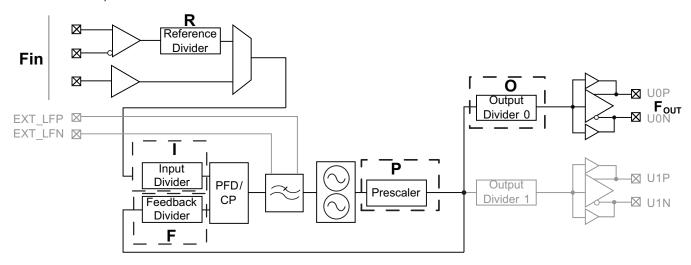


Figure 16. CDCE62002 Clock Path - Synthesizer

With respect to Figure 16, any output frequency generated by the CDCE62002 relates to the input frequency connected to the Synthesizer Block by Equation 1:

$$F_{OUT} = F_{IN} \cdot \frac{F}{R \cdot I \cdot O} \tag{1}$$

Equation 1 holds true subject to the constraints in Equation 2:

$$1.750GHz < O \cdot P \cdot F_{OUT} < 2.356GHz \tag{2}$$

And the comparison frequency F<sub>COMP</sub>,

$$40.0 \text{ kHz} \le F_{COMP} \le 40 \text{ MHz}$$

Where:

$$\mathsf{F}_{\mathsf{COMP}} = \frac{\mathsf{F}_{\mathsf{IN}}}{\mathsf{R} \cdot \mathsf{I}} \tag{3}$$

When AUX\_IN is selected as the input, R can be set to 1 in Equation 1 and Equation 3.



## 9.3 Feature Description

### 9.3.1 Phase Noise Analysis

Table 1. Phase Noise for 30.72-MHz External Reference

Phase Noise Specifications under following configuration: VCO = 1966.08 MHz, REF\_IN = 30.72 MHz, PFD Frequency = 30.72 MHz, Charge Pump Current = 1.5-mA Loop BW = 400 kHz at 3.3 V and 25°C. REFERENCE LVPECL-HP **LVCMOS** PHASE NOISE AT UNIT 491.52 MHz 30.72 MHz 491.52 MHz 491.52 MHz 122.88 MHz 10Hz -108 -84 -84 -85 -97 dBc/Hz 100Hz -130-98 -98 -97 -111 dBc/Hz 1kHz -134-106-106-106\_118 dBc/Hz 10kHz -152 -118 -118 -118 -130 dBc/Hz 100kHz -156 -121 -121 -121 -133 dBc/Hz 1MHz -157 dBc/Hz -131 -131 -130 -14210MHz \_ -146 -146 -145 -151 dBc/Hz 20MHz -145 -151 dBc/Hz -146 -146Jitter(RMS) 195 319 316 332.2 372.1 fs 10k~20MHz (10k~1MHz)

### Table 2. Phase Noise for 25-MHz Crystal Reference

Phase Noise Specifications under following configuration: VCO = 2000.00 MHz, AUX\_IN-REF = 25.00 MHz, PFD Frequency = 25.00 MHz, Charge Pump Current = 1.5-mA Loop BW = 400 kHz 3.3V and 25°C. LVCMOS LVPECL-HP LVDS **PHASE NOISE AT** UNIT 500.00 MHz 250.00 MHz 125.00 MHz 10Hz -72 -72 -79 dBc/Hz 100Hz -97 -97 -103dBc/Hz 1kHz -111 -111 -118 dBc/Hz 10kHz -120-120-126dBc/Hz 100kHz -124-124-130dBc/Hz 1MHz -136-136-142dBc/Hz 10MHz -147 -147-151 dBc/Hz 20MHz -148-148 -151 dBc/Hz Jitter(RMS) 10k~20MHz 426 426 443 fs

# 9.3.2 Output-to-Output Isolation

**Table 3. Output-to-Output Isolation** 

			WORST SPUR	UNIT			
The Output to Output Isolation was tested at 3.3-V supply and 25°C ambient temperature (Default Configuration):							
Output 1	Measured Channel	In LVDS Signaling at 125 MHz	-70	dB			
Output 0	Aggressor Channel	LVPECL 156.25 MHz					



#### 9.3.3 Device Control

Figure 17 provides a conceptual explanation of the CDCE62002 Device operation. Table 4 defines how the device behaves in each of the operational states.

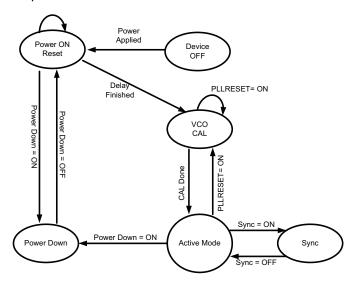


Figure 17. CDCE62002 Device State Control Diagram

Table 4 CDCF62002 Device State Definition	Tahla 1	CDCE62002	Device State	Definitions
---	---------	-----------	--------------	-------------

STATE	DEVICE BEHAVIOR	ENTERED VIA	EXITED VIA	SPI PORT STATU S	PLL STATU S	OUTPUT DIVIDER STATUS	OUTPUT BUFFER STATUS
Power-On Reset	After device power supply reaches approximately 2.35 V, the contents of EEPROM are copied into the Device Registers, thereby initializing the device hardware.	Power applied to the device or upon exit from Power-Down State through the $\overline{PD}$ pin set HIGH.	Power-On-Reset and EEPROM loading delays are finished OR the PD pin is set LOW.	OFF	Disabled	Disabled	OFF
VCO CAL	The voltage-controlled oscillator is calibrated based on the PLL settings and the incoming reference clock. After the VCO has been calibrated, the device enters Active Mode automatically.	Delay process in the Power-On Reset State is finished or PLLRESET=ON	Calibration Process in completed	ON	Enabled	Disabled	OFF
Active Mode	Normal Operation	CAL Done (VCO calibration process finished) or Sync = OFF (from Sync State).	Power Down or PLLRESET=ON	ON	Enabled	Disabled or Enabled	Disabled or Enabled
Power Down	Used to shut down all hardware and Resets the device after exiting the Power-Down State. Therefore, the EEPROM contents will eventually be copied into RAM after the Power-Down State is exited.	PD pin is pulled LOW.	PD pin is pulled HIGH.	ON	Disabled	Disabled	Disabled
Sync	Sync synchronizes both outputs dividers so that they begin counting at the same time	Sync Bit in device register 2 bit 8 is set LOW	Sync bit in device register 2 bit 8 is set HIGH	ON	Enabled	Disabled	Disabled

#### 9.3.4 External Control Pins

# Power Down (PD)

When pulled LOW,  $\overline{PD}$  activates the power-down state which shuts down all hardware and resets the device. Restoring  $\overline{PD}$  high will cause the CDCE62002 to exit the power-down state. This causes the device to behave as if it has been powered up including copying the EEPROM contents into RAM.  $\overline{PD}$  pin also has a shadowed  $\overline{PD}$  bit residing in Register 2 Bit 7. When asserted Low it puts the device in power-down mode, but it does not load the EEPROM when the bits is disserted.



#### NOTE

The SPI\_LE signal <u>has</u> to be high in order for the EEPROM to load correctly into RAM on the Rising edge of PD Pin.

### 9.3.4.1 Factory Default Programming

The CDCE62002 is factory pre-programmed to work with 25-MHz input from the reference input or from the auxiliary input with auto switching enabled. An internal PFD of 6.25 MHz and about 400-KHz loop bandwidth. Output 0 is pre-programmed as an LVPECL driver to output 156.25 MHz and output 1 is pre-programmed as LVDS driver to output 125 MHz.

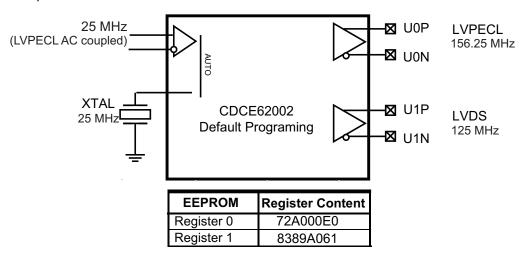


Figure 18. CDCE62002 Default Factory Programming

### 9.3.5 Input Block

The input block includes one universal input buffers, an auxiliary input, and a smart multiplexer.

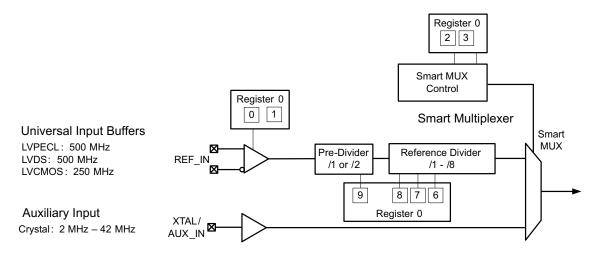


Figure 19. CDCE62002 Input Block With References to Registers

The CDCE62002 provides a reference divider that divides the clock exiting reference (REF\_IN) input buffer.

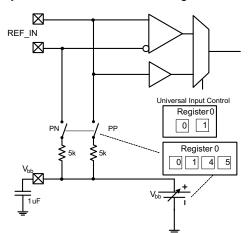
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Table 5. CDCE62002 Reference Divider Settings

		REFERENC	E DIVIDER		TOTAL
$\textbf{BIT NAME} \rightarrow$	REFDIVIDE3	REFDIVIDE2	REFDIVIDE1	REFDIVIDE0	DIVIDE RATIO
$\textbf{REGISTER BIT} \rightarrow$	0.9	0.8	0.7	0.6	ItATIO
	0	0	0	0	/1
	0	0	0	1	/2
	0	0	1	0	/3
	0	0	1	1	/4
	0	1	0	0	/5
	0	1	0	1	/6
	0	1	1	0	/7
	0	1	1	1	/8
	1	0	0	0	/2
	1	0	0	1	/4
	1	0	1	0	/6
	1	0	1	1	/8
	1	1	0	0	/10
	1	1	0	1	/12
	1	1	1	0	/14
	1	1	1	1	/16

### 9.3.5.1 Reference Input Buffer

Figure 20 shows the key elements of a universal input buffer (UIB). A UIB supports multiple formats along with different termination and coupling schemes. The CDCE62002 implements the UIB by including onboard switched termination, a programmable bias voltage generator, and a multiplexer. The CDCE62002 provides a high degree of configurability on the UIB to facilitate most existing clock input formats. REF\_IN only provides biasing internally. TI recommends terminating it externally if needed.



TERMSEL	INBUFSELY	INBUFSELX	ACDCSEL	Р	N	VBB	Input buffer Mode
	-1	0	0			1.9V	LVPECL – AC coupled
	'	0	1	ON	ON	1.2V	note (1)
0	0	1	0	OIN	OIV	1.2V	LVDS – AC coupled
		'	1			1.2V	LVDS – DC coupled
	1	1	X	OFF	OFF		LVCMOS
1	X	X X		X			Input Buffer Termination Disabled

note (1): This setting is not recommended.

Figure 20. CDCE62002 Universal Input Buffer



### 9.3.5.2 Smart Multiplexer Dividers

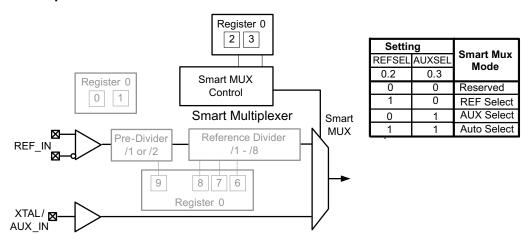


Figure 21. CDCE62002 Smart Multiplexer

In auto select mode the smart Mux switches automatically between reference input and auxiliary input with a preference to the reference input. In order for the smart MUX to function correctly the frequency after the reference divider and the auxiliary input signal frequency should be within 20% of each other or one of them should be zero or ground. In REF select mode, TI recommends connecting AUX\_IN to GND with a 1-k pulldown resistor. In AUX Select mode, TI recommends pulling the REF\_INp high and REF\_INn low with a 1-k resistor each.

### 9.3.5.3 Auxiliary Input Port

The auxiliary input on the CDCE62002 is designed to connect to an AT-Cut Crystal with a total load capacitance of 8 pF to 10 pF. One side of the crystal connects to ground while the other side connects to the auxiliary input of the device. The circuit accepts crystals from 2 to 42 MHz. See the Crystal Input Interface section for crystal load selection.

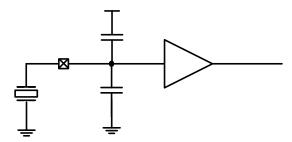


Figure 22. CDCE62002 Auxiliary Input Port

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### 9.3.5.4 Output Block

The output block includes two identical output channels. Each output channel comprises of a clock divider module, and a universal output buffer as shown in Figure 23.

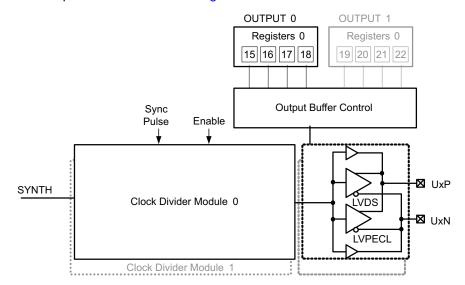


Figure 23. CDCE62002 Output Channel

Table 6. CDCE62002 Output Divider Settings

		OUTPUT DIVID	ERS SETTING		
DIVIDER 0 $\rightarrow$	0.18	0.17	0.16	0.15	DIVIDE RATIO
DIVIDER 1 →	0.22	0.21	0.20	0.19	
	0	0	0	0	Disabled
	0	0	0	1	/1
	0	0	1	0	/2
	0	0	1	1	/3
	0	1	0	0	/4
	0	1	0	1	/5
	0	1	1	0	/6
	0	1	1	1	Disabled
	1	0	0	0	/8
	1	0	0	1	Disabled
	1	0	1	0	/10
	1	0	1	1	/20
	1	1	0	0	/12
	1	1	0	1	/24
	1	1	1	0	/16
	1	1	1	1	/32



### 9.3.5.5 Synthesizer Block

Figure 24 provides an overview of the CDCE62002 synthesizer block. The synthesizer block provides a phase-locked loop, a partially integrated programmable loop filter, and two voltage-controlled oscillators (VCO). The synthesizer block generates an output clock called SYNTH and drives it onto the Internal clock distribution bus.

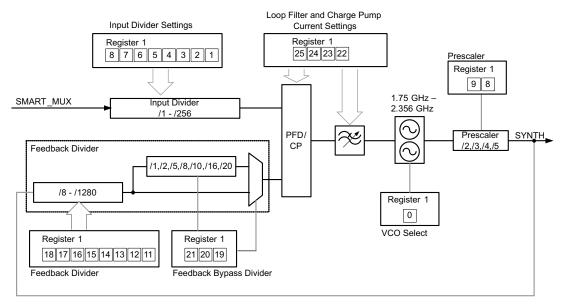


Figure 24. CDCE62002 Synthesizer Block

#### 9.3.5.6 Input Divider

The input divider divides the clock signal selected by the smart multiplexer and presents the divided signal to the phase frequency detector / charge pump of the frequency synthesizer.

**INPUT DIVIDER SETTINGS** DIVIDE **SELINDIV7 SELINDIV6 SELINDIV5** SELINDIV4 **SELINDIV3 SELINDIV2 SELINDIV1 SELINDIVO RATIO** 1.2 1.8 1.7 1.6 1.5 1.4 1.3 1.1 

Table 7. CDCE62002 Input Divider Settings

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# 9.3.5.7 Feedback and Feedback Bypass Divider

Table 8 shows how to configure the feedback divider for various divide values:

Table 8. CDCE62002 Feedback Divider Settings

			FEEDBAC	K DIVIDER				
SELFBDIV7	SELFBDIV6	SELFBDIV5	SELFBDIV4	SELFBDIV3	SELFBDIV2	SELFBDIV1	SELFBDIV0	DIVIDE
1.18	1.17	1.16	1.15	1.14	1.13	1.12	1.11	RATIO
0	0	0	0	0	0	0	0	8
0	0	0	0	0	0	0	1	12
0	0	0	0	0	0	1	0	16
0	0	0	0	0	0	1	1	20
0	0	0	0	0	1	0	1	24
0	0	0	0	0	1	1	0	32
0	0	0	0	1	0	0	1	36
0	0	0	0	0	1	1	1	40
0	0	0	0	1	0	1	0	48
0	0	0	1	1	0	0	0	56
0	0	0	0	1	0	1	1	60
0	0	0	0	1	1	1	0	64
0	0	0	1	0	1	0	1	72
0	0	0	0	1	1	1	1	80
0	0	0	1	1	0	0	1	84
0	0	0	1	0	1	1	0	96
0	0	0	1	0	0	1	1	100
0	1	0	0	1	0	0	1	108
0	0	0	1	1	0	1	0	112
0	0	0	1	0	1	1	1	120
0	0	0	1	1	1	1	0	128
0	0	0	1	1	0	1	1	140
0	0	1	1	0	1	0	1	144
0	0	0	1	1	1	1	1	160
0	0	1	1	1	0	0	1	168
0	1	0	0	1	0	1	1	180
0	0	1	1	0	1	1	0	192
0	0	1	1	0	0	1	1	200
0	1	0	1	0	1	0	1	216
0	0	1	1	1	0	1	0	224
0	0	1	1	0	1	1	1	240
0	1	0	1	1	0	0	1	252
0	0	1	1	1	1	1	0	256
0	0	1	1	1	0	1	1	280
0	1	0	1	0	1	1	0	288
0	1	0	1	0	0	1	1	300
0	0	1	1	1	1	1	1	320
0	1	0	1	1	0	1	0	336
0	1	0	1	0	1	1	1	360
0	1	0	1	1	1	1	0	384
1	1	0	1	1	0	0	0	392
0	1	1	1	0	0	1	1	400

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# Table 8. CDCE62002 Feedback Divider Settings (continued)

			FEEDBAC	K DIVIDER				
SELFBDIV7	SELFBDIV6	SELFBDIV5	SELFBDIV4	SELFBDIV3	SELFBDIV2	SELFBDIV1	SELFBDIV0	DIVIDE RATIO
1.18	1.17	1.16	1.15	1.14	1.13	1.12	1.11	KATIO
0	1	0	1	1	0	1	1	420
1	0	1	1	0	1	0	1	432
0	1	1	1	1	0	1	0	448
0	1	0	1	1	1	1	1	480
1	0	0	1	0	0	1	1	500
1	0	1	1	1	0	0	1	504
0	1	1	1	1	1	1	0	512
0	1	1	1	1	0	1	1	560
1	0	1	1	0	1	1	0	576
1	1	0	1	1	0	0	1	588
1	0	0	1	0	1	1	1	600
0	1	1	1	1	1	1	1	640
1	0	1	1	1	0	1	0	672
1	0	0	1	1	0	1	1	700
1	0	1	1	0	1	1	1	720
1	0	1	1	1	1	1	0	768
1	1	0	1	1	0	1	0	784
1	0	0	1	1	1	1	1	800
1	0	1	1	1	0	1	1	840
1	1	0	1	1	1	1	0	896
1	0	1	1	1	1	1	1	960
1	1	0	1	1	0	1	1	980
1	1	1	1	1	1	1	0	1024
1	1	0	1	1	1	1	1	1120
1	1	1	1	1	1	1	1	1280

Table 9 shows how to configure the Feedback Bypass Divider.



Table 9. CDCE62002 Feedback Bypass Divider Settings

FE							
SELBPDIV2	SELBPDIV1	SELBPDIV0	DIVIDE RATIO				
1.21	1.20	1.19					
0	0	0	2				
0	0	1	5				
0	1	0	8				
0	1	1	10				
1	0	0	16				
1	0	1	20				
1	1	0	RESERVED				
1	1	1	1(bypass)				

### 9.3.5.7.1 VCO Select

Table 10 illustrates how to control the dual voltage controlled oscillators.

Table 10. CDCE62002 VCO Select

BIT NAME →	VCO SELECT SELVCO	VCO CHARACTERISTICS											
$\textbf{REGISTER NAME} \rightarrow$	1.0	VCO RANGE	Fmin (MHz)	Fmax (MHz)									
	0	Low	1750	2046									
	1	High	2040	2356									

#### 9.3.5.7.2 Prescaler

Table 11 shows how to configure the prescaler.

**Table 11. CDCE62002 Prescaler Settings** 

SETT								
SELPRESCB	SELPRESCA	DIVIDE RATIO						
1.10	1.9							
0	0	5						
1	0	4						
0	1	3						
1	1	2						



#### 9.3.5.7.3 Loop Filter

Figure 25 depicts the loop filter topology of the CDCE62002. It facilitates both internal and external implementations providing optimal flexibility.

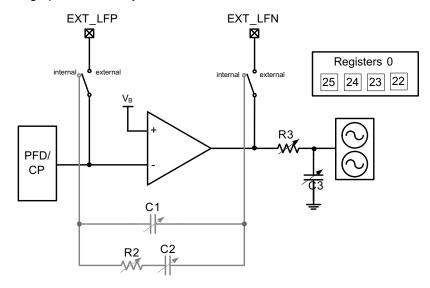


Figure 25. CDCE62002 Loop Filter Topology

## 9.3.5.8 Internal Loop Filter Component Configuration

Figure 25 illustrates the switching between four fixed internal loop filter settings and the external loop filter setting. Table 12 shows that the CDCE62002 has 16 settings different settings for the loop filter. Four of the settings are internal and twelve are external.

	LFRCSEL													
3	2	1	0	Loop Filter	C1	C2	R2	R3	C3	Current				
0	0	0	0	Internal	1.5 pF	473.5 pF	4.0k	5k	2.5 pF	1.5 mA				
0	0	0	1	Internal	1.5 pF	473.5 pF	4.0k	5k	2.5 pF	400 μΑ				
0	0	1	0	Internal	1.5 pF	473.5 pF	2.7k	5k	2.5 pF	250 μΑ				
0	0	1	1	Internal	1.5 pF	473.5 pF	2.7k	5k	2.5 pF	150 μΑ				
0	1	0	0	External	Х	X	Х	20k	112 pF	1.0 mA				
0	1	0	1	External	Х	X	Х	20k	112 pF	2.0 mA				
0	1	1	0	External	Х	Х	Х	20k	112 pF	3.0 mA				
0	1	1	1	External	Х	X	Х	20k	112 pF	3.75 mA				
1	0	0	0	External	Х	X	Х	10k	100 pF	1.0 mA				
1	0	0	1	External	Х	X	Х	10k	100 pF	2.0 mA				
1	0	1	0	External	Х	X	Х	10k	100 pF	3.0 mA				
1	0	1	1	External	Х	Х	Х	10k	100 pF	3.75 mA				
1	1	0	0	External	Х	X	Х	5k	100 pF	1.0 mA				
1	1	0	1	External	Х	Х	Х	5k	64 pF	2.0 mA				
1	1	1	0	External	Х	X	Х	5k	48 pF	3.0 mA				
1	1	1	1	External	Х	X	Х	5k	38 pF	3.75 mA				

Table 12. CDCE62002 Loop Filter Settings



#### 9.3.6 Lock Detect

The CDCE62002 provides a lock detect indicator circuit that can be detected on an external Pin PLL\_LOCK (Pin 32) and internally by reading PLLLOCKPIN bit (6) in Register 2.

Two signals whose phase difference is less than a prescribed amount are *locked* otherwise they are *unlocked*. The phase frequency detector / charge pump compares the clock provided by the input divider and the feedback divider; using the input divider as the phase reference. The lock detect circuit implements a programmable lock detect window. Table 13 shows an overview of how to configure the lock detect feature. The PLL\_LOCK pin will possibly jitter several times between lock and out of lock until the PLL achieves a stable lock. If desired, choosing a wide loop bandwidth and a high number of successive clock cycles virtually eliminates this characteristic. PLL LOCK will return to out of lock, if just one cycle is outside the lock detect window or if a cycle slip occurs.

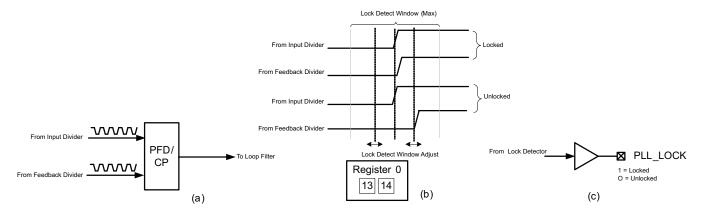


Figure 26. CDCE62002 Lock Detect

LOCK DETECT LOCK DETECT LOCKW(0) BIT NAME → LOCKW(1) **WINDOW** REGISTER NAME  $\rightarrow$ 0.13 0.14 0 0 2.1 ns 0 1 4.6 ns 1 0 7.2 ns 1 1 19.9 ns

Table 13. CDCE62002 Lock Detect Control

## 9.3.7 Crystal Input Interface

In fundamental mode, TI recommends the oscillation mode of operation for the input crystal and parallel resonance is the recommended type of circuit for the crystal.

A crystal load capacitance refers to all capacitances in the oscillator feedback loop. It is equal to the amount of capacitance seen between the terminals of the crystal in the circuit. For parallel resonant mode circuits, the correct load capacitance is necessary to ensure the oscillation of the crystal within the expected parameters.

The CDCE62002 implements an input crystal oscillator circuitry, known as the Colpitts oscillator, and requires one pad of the crystal to interface with the AUX\_IN pin; the other pad of the crystal is tied to ground. In this crystal interface, it is important to account for all sources of capacitance when calculating the correct value for the discrete capacitor component, CL, for a design.

The CDCE62002 has been characterized with 10-pF parallel resonant crystals. The input crystal oscillator stage in the CDCE62002 is designed to oscillate at the correct frequency for all parallel resonant crystals with low-pull capability and rated with a load capacitance that is equal to the sum of the on-chip load capacitance at the AUX\_IN pin (10-pF), crystal stray capacitance, and board parasitic capacitance between the crystal and AUX\_IN pin.



The normalized frequency error of the crystal, as a result of load capacitance mismatch, can be calculated as Equation 4:

$$\frac{\Delta f}{f} = \frac{C_S}{2(C_{L,R} + C_O)} - \frac{C_S}{2(C_{L,A} + C_O)}$$

#### where

- C<sub>S</sub> is the motional capacitance of the crystal
- C<sub>0</sub> is the shunt capacitance of the crystal
- C<sub>I,R</sub> is the rated load capacitance for the crystal
- C<sub>LA</sub> is the actual load capacitance in the implemented PCB for the crystal
- Δf is the frequency error of the crystal
- f is the rated frequency of the crystal

(4)

The first three parameters can be obtained from the crystal vendor.

To minimize the frequency error of the crystal to meet application requirements, the difference between the rated load capacitance and the actual load capacitance must be minimized and a crystal with low-pull capability (low CS) must be used.

For example, if an application requires less than  $\pm 50$ -ppm frequency error and a crystal with less than  $\pm 50$ -ppm frequency tolerance is picked, the characteristics are as follows:  $C_0 = 7$  pF,  $C_S = 10$  pF, and  $C_{L,R} = 12$  pF. To meet the required frequency error, calculate  $C_{L,A}$  using Equation 4 to be 17 pF. Subtracting  $C_{L,R}$  from  $C_{L,A}$ , results in 5 pF; take care during printed-circuit board (PCB) layout with the crystal and the CDCE62002 to ensure that the sum of the crystal stray capacitance and board parasitic capacitance is less than the calculated 5 pF.

Good layout practices are fundamental to the correct operation and reliability of the oscillator. It is critical to place the crystal components very close to the XIN pin to minimize routing distances. Long traces in the oscillator circuit are a very common source of problems. Do not route other signals across the oscillator circuit. Also, make sure power and high-frequency traces are routed as far away as possible to avoid crosstalk and noise coupling. Avoid the use of vias; if the routing becomes very complex, it is better to use  $0-\Omega$  resistors as bridges to go over other signals. Vias in the oscillator circuit must only be used for connections to the ground plane. Do not share ground connections; instead, make a separate connection to ground for each component that requires grounding. If possible, place multiple vias in parallel for each connection to the ground plane. Especially in the Colpitts oscillator configuration, the oscillator is very sensitive to capacitance in parallel with the crystal. Therefore, the layout must be designed to minimize stray capacitance across the crystal to less than 5 pF total under all circumstances to ensure proper crystal oscillation. Be sure to take into account both PCB and crystal stray capacitance.

#### 9.3.8 VCO Calibration

The CDCE62002 includes two on-chip LC oscillator-based VCOs with low phase noise covering a frequency range of 1.75 GHz to 2.356 GHz. The VCO must be calibrated to ensure proper operation over the valid device operating conditions. VCO calibration is controlled by the reference clock input. This calibration requires that the PLL be set up properly to lock the PLL loop and that the reference clock input be present.

The device enters self-calibration of the VCO automatically at power up, after the registers have been loaded from the EEPROM and an input clock signal is detected. If there is no input clock available during power up, the VCO will wait for reference clock before starting calibration.

If the input signal is not valid during self-calibration, it is necessary to re-initiate VCO calibration after the input clock signal stabilizes.

### NOTE

Re-calibration is also necessary anytime a PLL setting is changed (e.g. divider ratios in the PLL or loop filter settings are adjusted).

VCO calibration can be initiated by writing to register 2 bits 7, 13 and 20.



# Table 14. VCO Calibration Method Through Register Programming

CALSELECT Reg 2.13	PLLRESET 2.20	PD 2.7	VCO CALIBRATION MECHANISM <sup>(1)</sup>
1	1-0-1	1	VCO calibration starts at PLLRESET toggling low-to-high. The outputs turn off for the duration of the calibration, which is a few ns.
0	х	1-0-1	Device is powered down when $\overline{PD}$ is toggle 1-to-0. All outputs are disabled while $\overline{PD}$ is zero. After asserting $\overline{PD}$ from zero to one the VCO becomes calibrated and immediately afterwards the device outputs turn on.

<sup>(1)</sup> A VCO calibration is also initiated if the external PD pin is toggle high-low-high. In this case all EEPROM registers become reloaded into the device and the CALSELECT bit is reset to 0.

## 9.3.9 Start-Up Time Estimation

The CDCE62002 startup time can be estimated based on the parameters defined in Table 15 and graphically shown in Figure 27.

**Table 15. Start-up Time Dependencies** 

	PARAMETER	DESCRIPTION	METHOD OF DETERMINATION
t <sub>pul</sub>	Power-up time (low limit)	Power-supply rise time to low limit of power-on- reset (POR) trip point	Time required for power supply to ramp to 2.27 V
t <sub>puh</sub>	Power-up time (high limit)	Power-supply rise time to high limit of power-on- reset (POR) trip point	Time required for power supply to ramp to 2.64 V
t <sub>rsu</sub>	Reference start-up time	After POR releases, the Colpitts oscillator is enabled. This start-up time is required for the oscillator to generate the requisite signal levels for the delay block to be clocked by the reference input	500 μs best-case and 800 μs worst-case (This is only for crystal connected to AUX_IN)
t <sub>delay</sub>	Delay time	Internal delay time generated from the clock. This delay provides time for the oscillator to stabilize.	$t_{delay}$ = 16384 x $t_{id}$ $t_{id}$ = period of input clock to the input divider
t <sub>VCO_CAL</sub>	VCO calibration time	VCO calibration time generated from the PFD clock. This process selects the operating point for the VCO based on the PLL settings.	t <sub>VCO_CAL</sub> = 550 x t <sub>PFD</sub> t <sub>PFD</sub> = period of the PFD clock
t <sub>PLL_LOCK</sub>	PLL lock time	Time required for PLL to lock within ±10 ppm of reference frequency	t <sub>PLL_LOCK</sub> = 3/LBW LBW = PLL Loop Bandwidth

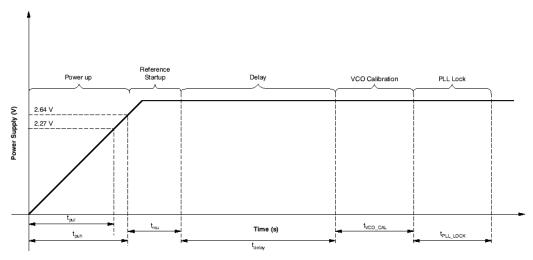


Figure 27. Start-Up Time dependencies



#### 9.4 Device Functional Modes

#### 9.4.1 Clock Generator

The CDCE62002 can generate 1 to 4 low noise clocks from a single crystal or crystal oscillator as follows:

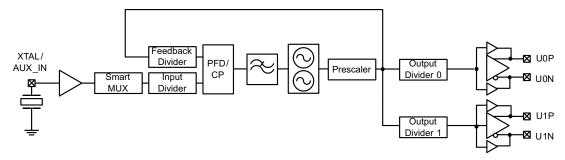


Figure 28. CDCE62002 as a Clock Generator

# 9.4.2 SERDES Start-Up and Clock Cleaner

The CDCE62002 can serve as a SERDES device companion by providing a crystal based reference for the SERDES device to lock to receive data stream and when the SERDES locks to the data and outputs the recovered clock the CDCE62002 can switch and use the recovered clock and serve as a jitter cleaner.

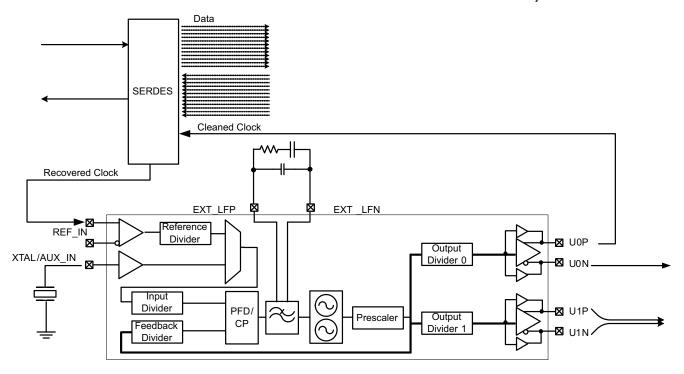


Figure 29. CDCE62002 Clocking SERDES

Because the jitter of the recovered clock can be above 100 ps (RMS), the output jitter from CDCE62002 can be as low and 6 ps (RMS) depending on the external loop filter configuration.

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## **Device Functional Modes (continued)**

### 9.4.3 Clocking ADCS With the CDCE62002

High-speed analog to digital converters incorporate high input bandwidth on both the analog port and the sample clock port. Often the input bandwidth far exceeds the sample rate of the converter. Engineers regularly implement receiver chains that take advantage of the characteristics of bandpass sampling. This implementation trend often causes engineers working in communications system design to encounter the term *clock-limited performance*. Therefore, it is important to understand the impact of clock jitter on ADC performance. Equation 5 shows the relationship of data converter signal to noise ratio (SNR) to total jitter:

$$SNR_{jitter} = 20log_{10} \left[ \frac{1}{2\pi f_{in} jitter_{total}} \right]$$
(5)

Total jitter comprises two components: the intrinsic aperture jitter of the converter and the jitter of the sample clock:

$$jitter_{total} = \sqrt{\left(jitter_{ADC}\right)^2 + \left(jitter_{CLK}\right)^2}$$
(6)

With respect to an ADC with N-bits of resolution, ignoring total jitter, ADC quantization error, and input noise, Equation 7 shows the relationship between resolution and SNR:

$$SNR_{ADC} = 6.02N + 1.76$$
 (7)

Figure 30 plots Equation 5 and Equation 7 for constant values of total jitter. When used in conjunction with most ADCs, the CDCE62002 supports a total jitter performance value of <1 ps.

#### **Data Converter Jitter Requirements**

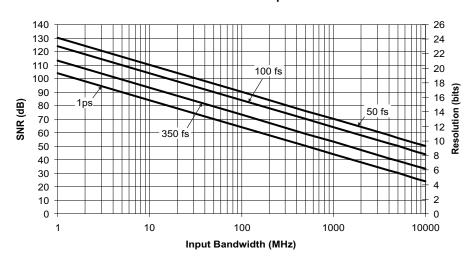


Figure 30. Data Converter Jitter Requirements



## 9.5 Programming

#### 9.5.1 Interface and Control Block

The interface and control block includes a SPI interface, one control pin, a non-volatile memory array in which the device stores default configuration data, and an array of device registers implemented in static RAM. This RAM, also called the device registers, configures all hardware within the CDCE62002.

### 9.5.1.1 SPI (Serial Peripheral Interface)

The serial interface of CDCE62002 is a simple bidirectional SPI interface for writing and reading to and from the device registers. It implements a low speed serial communications link in a master/slave topology in which the CDCE62002 is a slave. The SPI consists of four signals:

- SPI\_CLK:Serial Clock (Output from Master) the CDCE62002 and the master host clock data in and out on the rising edge of SPI\_CLK. Data transitions therefore occur on the falling edge of the clock. (LVCMOS Input Buffer)
- SPI MOSI: Master Output Slave Input (LVCMOS Input Buffer).
- SPI MISO: Master Input Slave Output (Open Drain LVCMOS Buffer)
- SPI\_LE: Latch Enable (Output from Master). The falling edge of SPI\_LE initiates a transfer. If SPI\_LE is high, no data transfer can take place. (LVCMOS Input Buffer).

#### 9.5.1.2 SPI Interface Master

The Interface master can be designed using a FPGA or a microcontroller. The CDCE62002 acts as a slave to the SPI master and only supports non-consecutive read and write command. The SPI clock should start and stop with respect to the SPI\_LE signal as shown in Figure 31 SPI\_MOSI, SPI\_CLK and SPI\_LE are generated by the SPI Master. SPI MISO is generated by the SPI slave the CDCE62002.

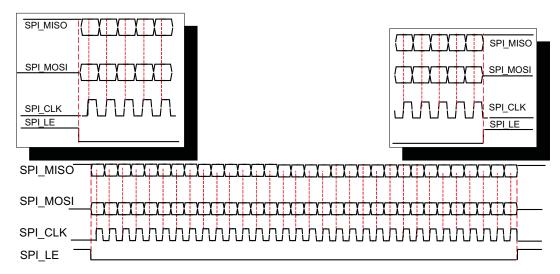


Figure 31. CDCE62002 SPI Read/Write Command

#### 9.5.1.3 SPI Consecutive Read/Write Cycles to the CDCE62002

Figure 32 Illustrates how two consecutive SPI cycles are performed between a SPI Master and the CDCE62002 SPI Slave.

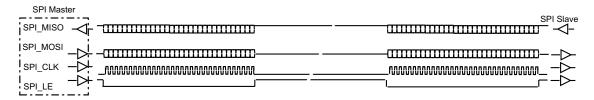


Figure 32. Consecutive Read/Write Cycles

# **Programming (continued)**

### 9.5.1.4 Writing to the CDCE62002

Figure 33 illustrates a Write to RAM operation. Notice that the latching of the first data bit in the data stream (Bit 0) occurs on the first rising edge of SPI\_CLK after SPI\_LE transitions from a high to a low. For the CDCE62002, data transitions occur on the falling edge of SPI\_CLK. A rising edge on SPI\_LE signals to the CDCE62002 that the transmission of the last bit in the stream (Bit 31) has occurred.

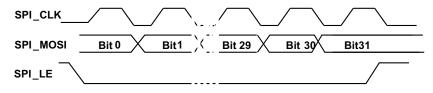


Figure 33. CDCE62002 SPI Write Operation

### 9.5.1.5 Reading from the CDCE62002

Figure 34 shows how the CDCE62002 executes a read command. The SPI master first issues a read command to initiate a data transfer from the CDCE62002 back to the host (see SPI Bus Timing Characteristics). This command specifies the address of the register of interest. By transitioning SPI\_LE from a low to a high, the CDCE62002 resolves the address specified in the appropriate bits of the data field. The host drives SPI\_LE low and the CDCE62002 presents the data present in the register specified in the read command on SPI MISO.

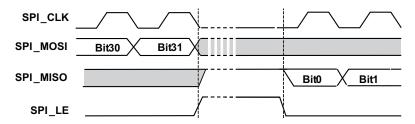


Figure 34. CDCE62002 SPI Read Operation

### 9.5.1.6 Writing to EEPROM

After the CDCE62002 detects a power-up and completes a reset cycle, the device copies the contents of the onchip EEPROM into the device registers. (SPI\_LE signal has to be HIGH in order for the EEPROM to load correctly during the rising edge of power\_down signal).

The host issues a special commands shown in Figure 35 to copy the contents of device registers 0 and 1into EERPOM.

Copy RAM to EEPROM – unlock, execution of this command can happen many times.

After the command is initiated, power must remain stable and the host must not access the CDCE62002 for at least 50 ms to allow the EEPROM to complete the write cycle and to avoid the possibility of EEPROM corruption.

#### 9.5.1.7 CDCE62002 SPI Command Structure

The CDCE62002 supports three commands issued by the master through the SPI:

- Write to RAM
- Read Command
- Copy RAM to EEPROM unlock

Figure 35 provides a summary of the CDCE62002 SPI command structure. The host (master) constructs a Write to RAM command by specifying the appropriate register address in the address field and appends this value to the beginning of the data field. Therefore, a valid command stream must include 32 bits, transmitted LSB first. The host must issue a read command to initiate a data transfer from the CDCE62002 back to the host. This command specifies the address of the register of interest in the data field.



# **Programming (continued)**

				Data Field (28 Bits)										Addr Field (4 Blts)																				
Register	Operation	NVM	2 7		2 5			2	2 1	2 0	1 9	1 8	1 7	1 6	1 5	1 4	1	1 2	1	1 0	9	8	7	6	5	4	3	2	1	0	3	2	1	0
0	Write to RAM	Yes	Х	Χ	Х	Χ	Х	Х	Х	Χ	Х	Х	Χ	Х	Х	Χ	Х	Χ	Х	Х	Х	Х	Х	Χ	Х	Х	Х	Χ	Х	Х	0	0	0	0
1	Write to RAM	Yes	Х	Χ	Х	Χ	Х	Х	Х	Χ	Х	Х	Χ	Х	Х	Х	Х	Χ	Χ	Х	Х	Х	Х	Χ	Χ	Х	Х	Χ	Х	Х	0	0	0	1
2	Status/Control	No	Х	Χ	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	Х	Χ	Х	Х	Χ	Х	Х	0	0	1	0
Instruction	Read Command	No	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	Α	Α	Α	Α	1	1	1	0
Instruction	RAM EEPROM	Unlock	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	1	1	1	1	1

NOTE: 'A' indicates address bits.

Figure 35. CDCE62002 SPI Command Structure

# 9.5.2 Device Configuration

The *Feature Description* section described four different functional blocks contained within the CDCE62002. Figure 36 depicts these blocks along with a high-level functional block diagram of the circuit elements comprising each block. The balance of this section focuses on a detailed discussion of each functional block from the perspective of how to configure them.

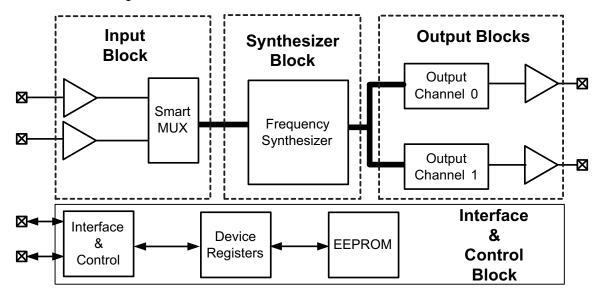


Figure 36. CDCE62002 Circuit Blocks



# 9.6 Register Maps

# 9.6.1 Device Registers: Register 0 Address 0x00

# Table 16. CDCE62002 Register 0 Bit Definitions

REGISTER BIT	BIT NAME	RELATED BLOCK	DESCRIPTION / FUNCTION						
0	INBUFSELX	INBUFSELX	Input Buffer Select (LVPECL,LVDS or LVCMOS)  XY(00 ) Disabled, (01) LVDS, (10) LVPECL, (11) LVCMOS  The VBB internal Bissing will be determined from this setting						
1	INBUFSELY	INBUFSELY	The VBB internal Biasing will be determined from this setting						
2	REFSEL		See specific section for more detailed description and configuration	EEPROM					
3	AUXSEL	Smart MUX Bits(2,3)	setup. 00 - RESERVED 10 - REF_IN Select 01- AUX_IN Select 11 - Auto Select ( Reference then AUX)	EEPROM					
4	ACDCSEL	Input Buffers	If Set to 1 DC Termination, If set to "0" AC Termination	EEPROM					
5	TERMSEL	Input Buffers	If Set to 0 Input Buffer Internal Termination Enabled	EEPROM					
6	REFDIVIDE 0			EEPROM					
7	REFDIVIDE 1		Reference Divider Settings (Refer to Table 5)	EEPROM					
8	REFDIVIDE 2	See specific section for more detailed description and configuration setup.		EEPROM					
9	REFDIVIDE 3			EEPROM					
10	RESERVED		Always Set to 0	EEPROM					
11	I70TEST	TEST	Set to 0 for Normal Operation.	EEPROM					
12	ATETEST	TEST	Set to 0 for Normal Operation.	EEPROM					
13	LOCKW(0)	PLL Lock	Lock-detect window Bit 0	EEPROM					
14	LOCKW(1)	PLL Lock	Lock-detect window Bit 1	EEPROM					
15	OUT0DIVRSEL0	Output 0		EEPROM					
16	OUT0DIVRSEL1	Output 0	Output 0 Divider Settings (Refer to Table 6)	EEPROM					
17	OUT0DIVRSEL2	Output 0	See specific section for more detailed description and configuration setup.	EEPROM					
18	OUT0DIVRSEL3	Output 0	·	EEPROM					
19	OUT1DIVRSEL0	Output 1		EEPROM					
20	OUT1DIVRSEL1	Output 1	Output 1 Divider Settings (Refer to Table 6)	EEPROM					
21	OUT1DIVRSEL2	Output 1	See specific section for more detailed description and configuration setup.	EEPROM					
22	OUT1DIVRSEL3	Output 1		EEPROM					
23	HIPERORMANCE	Output 0 & 1	High Performance, If this Bit is set to 1:  - Increases the Bias in the device to achieve Best Phase Noise on the Output Divider  - It changes the LVPECL Buffer to Hi Swing in LVPECL.  - It increases the current consumption by 20mA (Typical)  - This setting only applies to LVPECL output buffers. If none of these two outputs are LVPECL, this bit should be set to zero.	EEPROM					
24	OUTBUFSEL0X	Output 0	Output Buffer mode select for OUTPUT 0 .	EEPROM					
25	OUTBUFSEL0Y	Output 0	(X,Y)=00:Disabled, 01:LVCMOS, 10:LVDS, 11:LVPECL	EEPROM					
26	OUTBUFSEL1X	Output 1	Output Buffer mode select for OUTPUT 1 .	EEPROM					
27	OUTBUFSEL1Y	Output 1	(X,Y)=00:Disabled, 01:LVCMOS, 10:LVDS, 11:LVPECL	EEPROM					

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## Table 17. Reference Input AC/DC Input Termination Table

REFERENCE INPUT	REGISTER BITS		₹	VBB VOLTAGE	REF+ TERMINATION	REF- TERMINATION	
INTERNAL TERMINATION	0 1 4 5		5	GENERATOR	5kΩ to VBB	5kΩ to VBB	
External Termination	Х	Χ	Х	1	_	OPEN	OPEN
Disabled	0	0	Х	Х	_	OPEN	OPEN
LVCMOS	1	1	Х	0	_	OPEN	OPEN
LVPECL-AC	1	0	0	0	1.9 V	CLOSED	CLOSED
LVPECL-DC	1	0	1	0	1.0 V	CLOSED	CLOSED
LVDS-AC	0	1	0	0	1.2 V	CLOSED	CLOSED
LVDS-DC	0	1	1	0	1.2 V	CLOSED	CLOSED

## 9.6.2 Device Registers: Register 1 Address 0x01

## Table 18. CDCE62002 Register 1 Bit Definitions

			10. OD O LOZUOZ Register 1 DR Deminions				
REGISTER BIT	BIT NAME	RELATED BLOCK	DESCRIPTION / FUNCTION				
0	SELVCO	VCO Core	VCO Select – See Table 10 for details	EEPROM			
1	SELINDIV0	VCO Core		EEPROM			
2	SELINDIV1	VCO Core		EEPROM			
3	SELINDIV2	VCO Core		EEPROM			
4	SELINDIV3	VCO Core	Input Divider Settings (Refer to Table 7)	EEPROM			
5	SELINDIV4	VCO Core	See specific section for more detailed description and configuration setup.	EEPROM			
6	SELINDIV5	VCO Core		EEPROM			
7	SELINDIV6	VCO Core		EEPROM			
8	SELINDIV7	VCO Core					
9	SELPRESCA	VCO Core	PRESCALER Setting. (Refer to Table 11)	EEPROM			
10	SELPRESCB	VCO Core	See specific section for more detailed description and configuration setup.				
11	SELFBDIV0	VCO Core		EEPROM			
12	SELFBDIV1	VCO Core					
13	SELFBDIV2	VCO Core					
14	SELFBDIV3	VCO Core	FEEDBACK DIVIDER Setting (Refer to Table 8)	EEPROM			
15	SELFBDIV4	VCO Core	See specific section for more detailed description and configuration setup.				
16	SELFBDIV5	VCO Core		EEPROM			
17	SELFBDIV6	VCO Core		EEPROM			
18	SELFBDIV7	VCO Core		EEPROM			
19	SELBPDIV0	VCO Core		EEPROM			
20	SELBPDIV1	VCO Core		EEPROM			
21	SELBPDIV2	VCO Core	dotalled dosellphor and coringulation solup.	EEPROM			
22	LFRCSEL0	VCO Core		EEPROM			
23	LFRCSEL1	VCO Core	See specific section for more detailed description and configuration setup.  See specific section for more detailed description and configuration setup.  BYPASS DIVIDER Setting (Refer to Table 9) See specific section for more detailed description and configuration setup.  BYPASS DIVIDER Setting (Refer to Table 9) See specific section for more detailed description and configuration setup.  Loop Filter & Charge Pump Control Setting (Refer to Table 12)  See specific section for more detailed description and configuration setup.	EEPROM			
24	LFRCSEL2	VCO Core		EEPROM			
25	LFRCSEL3	VCO Core	7				
26	RESERVED	Status	TI Use Only; set 0	EEPROM			
27	RESERVED	Status	Read Only; May read back to 1 or 0; set '1' while writing	EEPROM			



## 9.6.3 Device Registers: Register 2 Address 0x02

## Table 19. CDCE62002 Register 2 Bit Definitions

REGISTER BIT	BIT NAME	RELATED BLOCK	DESCRIPTION / FUNCTION	
0	RESERVED	Diagnostics	TI Test Registers. For TI Use Only	RAM
1	RESERVED	Diagnostics	TI Test Registers. For TI Use Only	RAM
2	RESERVED	Diagnostics	TI Test Registers. For TI Use Only	RAM
3	RESERVED	Diagnostics	TI Test Registers. For TI Use Only	RAM
4	RESERVED	Diagnostics	TI Test Registers. For TI Use Only	RAM
5	RESERVED	Diagnostics	TI Test Registers. For TI Use Only	RAM
6	PLLLOCKPIN	Status	Read only: Status of the PLL Lock Pin Driven by the device. PLL Lock = 1	RAM
7	PD	Control	Power-down mode "On" when set to 0, Off when set to "1" is normal operation (PD bit does not load the EEPROM into RAM when set to "1").	RAM
8	SYNC	Control	If toggled 1-0-1 this bit forces "SYNC" resynchronize the Output Dividers.	RAM
9	RESERVED	Diagnostics	TI Test Registers. For TI Use Only	RAM
10	VERSION0	Read Only		RAM
11	VERSION1	Read Only		RAM
12	VERSION2	Read Only		RAM
13	CALSELECT	VCO Core	This bit selects the VCO calibration mode. If CALSELECT = 0 , toggling PD# bit (Register 2 bit 7) will calibrate the VCO. When CALSELECT = 1, toggling the PLLRESET bit (Register 2 bit 20) will calibrate the VCO. Default value = 0	RAM
14	RESERVED	Diagnostics	TI Test Registers. For TI Use Only	RAM
15	RESERVED	Diagnostics	TI Test Registers. For TI Use Only	RAM
16	RESERVED	Diagnostics	TI Test Registers. For TI Use Only	RAM
17	RESERVED	Diagnostics	TI Test Registers. For TI Use Only	RAM
18	RESERVED	Diagnostics	TI Test Registers. For TI Use Only	RAM
19	RESERVED	Diagnostics	TI Test Registers. For TI Use Only	RAM
20	PLLRESET	Diagnostics	When CALSELECT=1 this bit forces a VCO calibration when toggled 1-0-1. If CALSELECT=0 this bit is ignored.	RAM
21	TITSTCFG0	Diagnostics	TI Test Registers. For TI Use Only	RAM
22	TITSTCFG1	Diagnostics	TI Test Registers. For TI Use Only	RAM
23	TITSTCFG2	Diagnostics	TI Test Registers. For TI Use Only	RAM
24	TITSTCFG3	Diagnostics	TI Test Registers. For TI Use Only	RAM
25	RESERVED	Diagnostics	TI Test Registers. For TI Use Only	RAM
26	RESERVED	Diagnostics	TI Test Registers. For TI Use Only	RAM
27	RESERVED	Diagnostics	TI Test Registers. For TI Use Only	RAM



## 10 Power Supply Recommendations

The CDCE62002 is a high-performance device; therefore pay careful attention to device configuration and printed-circuit board layout with respect to power consumption. Table 20 provides the power consumption for the individual blocks within the CDCE62002. To estimate total power consumption, calculate the sum of the products of the number of blocks used and the power dissipated of each corresponding block.

		· · · · ·
INTERNAL BLOCK (Power at 3.3 V)	POWER DISSIPATED PER BLOCK (mW)	NUMBER OF BLOCKS PER DEVICE
Input circuit	32	1
PLL and VCO core	333	1
Output divider	92	2
Output buffer ( LVPECL)	150	2
Output buffer (LVDS)	95	2
Output buffer (LVCMOS)	62	4

Table 20. CDCE62002 Power Consumption

This power estimate determines the degree of thermal management required for a specific design. Observing good thermal layout practices enables the thermal pad on the backside of the 32-pin VQFN package to provide a good thermal path between the die contained within the package and the ambient air. This thermal pad also serves as the ground connection the device; therefore, a low inductance connection to the ground plane is essential.

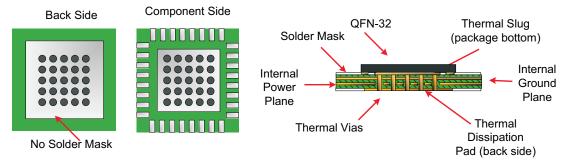


Figure 37. CDCE62002 Recommended PCB Layout



### 11 Layout

### 11.1 Layout Guidelines

Figure 38 shows a conceptual layout focusing on power supply bypass capacitor placement. If the capacitors are mounted on the back side, 0402 components can be employed; however, soldering to the thermal dissipation pad can be difficult. If the capacitors are mounted on the component side, 0201 components must be used to facilitate signal routing. In either case, the connections between the capacitor and the power supply terminal on the device must be kept as short as possible.

### 11.2 Layout Example

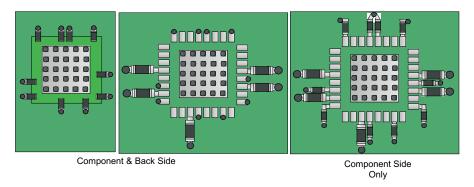


Figure 38. CDCE62002 Power Supply Bypassing



## 12 Device and Documentation Support

#### 12.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### 12.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

#### 12.3 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

#### 12.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### 12.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

### 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

#### 13.1 Package

The CDCE62002 is packaged in a 32-Pin Lead Free "Green" Plastic Quad Flatpack Package with enhanced bottom thermal pad for heat dissipation. The Texas Instruments Package Designator is; RHB (S-PQFP-N32). Please refer to the Mechanical Data appendix at the end of this document for more information.

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## **PACKAGE OPTION ADDENDUM**

10-Dec-2020

#### PACKAGING INFORMATION

www.ti.com

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
CDCE62002RHBR	ACTIVE	VQFN	RHB	32	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CDCE 62002	Samples
CDCE62002RHBT	ACTIVE	VQFN	RHB	32	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CDCE 62002	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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10-Dec-2020

## PACKAGE MATERIALS INFORMATION

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## TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

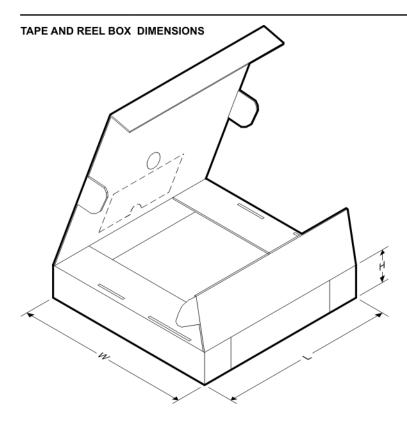
### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CDCE62002RHBR	VQFN	RHB	32	3000	330.0	12.4	5.3	5.3	1.5	8.0	12.0	Q2

www.ti.com 1-Sep-2021



#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
CDCE62002RHBR	VQFN	RHB	32	3000	350.0	350.0	43.0	

5 x 5, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD



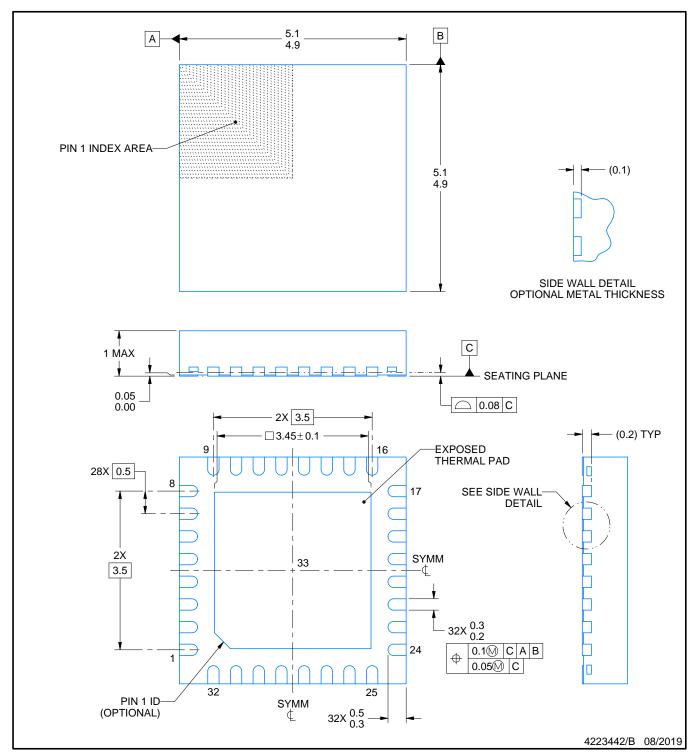
Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4224745/A





PLASTIC QUAD FLATPACK - NO LEAD



#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
  2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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LMK04808BISQX/NOPB MK2049-34SAILF CDCE937QPWRQ1 CDCE913QPWRQ1 8T49N286A-998NLGI 83PN156DKILF
954101DFLF 954201BFLF 954206AGLF SI5324E-C-GM SI5324D-C-GM LMK04808BISQ/NOPB 9LRS3165BGLFT 83PN15639ANRGI
9FG108EFILFT 843256BGLF 932S208DGLFT 841N4830BKILF LMK04133SQE/NOPB SI5383B-D00100-GM 951462AGLFT SI5374CA-GL 9FG108EFLFT 9FGP204BKLF 8T49N285A-998NLGI ABMJB-903-101UMG-T5 ABMJB-903-150UMG-T5 ABMJB-903-151UMGT5 AD9837ACPZ-RL7 AD9837BCPZ-RL7 9FG108EGILF 9FG108EGLFT 9FG108EGILFT CS2000P-CZZ CS2100CP-CZZ